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Kind regards,

Team Nexperia

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small DFN1608D-2 (SOD1608) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 2 A
- Reverse voltage: V_R ≤ 40 V
- Low forward voltage V_F ≤ 660 mV
- Low reverse current
- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{sp} \le$ 130 °C; square wave		-	-	2	Α
		δ = 0.5; f = 20 kHz; $T_{amb} \le 25$ °C; square wave	[1]	-	-	2	Α
V _R	reverse voltage	T _j = 25 °C		-	-	40	V
V _F	forward voltage	I_F = 2 A; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_j = 25 °C		-	585	660	mV





40 V, 2 A low VF MEGA Schottky barrier rectifier

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _R	reverse current	V _R = 10 V; T _j = 25 °C	-	1	5	μΑ
t _{rr}	reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	4	-	ns

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		1 [[-] 2
2	Α	anode	1 2	sym001
			Transparent top view DFN1608D-2 (SOD1608)	

[1] The marking bar indicates the cathode.

6. Ordering information

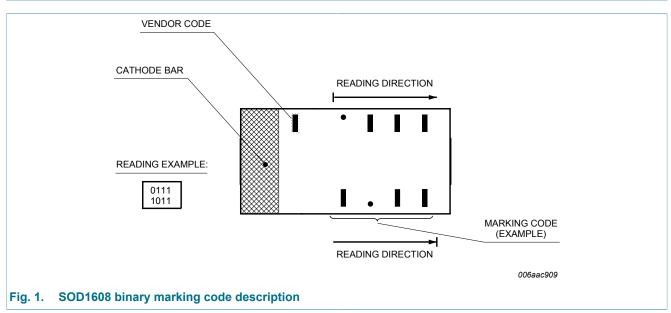
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMEG4020EPK	DFN1608D-2	DFN1608D-2: leadless ultra small plastic package; 2 terminals	SOD1608		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG4020EPK	0001 0000



8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C		-	40	V
I _F	forward current	T _{sp} ≤ 125 °C		-	2.83	Α
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{sp} \le$ 130 °C; square wave		-	2	A
		$\bar{\delta}$ = 0.5; f = 20 kHz; $T_{amb} \leq$ 25 °C; square wave	[1]	-	2	А
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.25$		-	4	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	415	mW
			[3]	-	895	mW
			[1]	-	1565	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1][2]	-	-	300	K/W
				-	-	140	K/W
			[1][4]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	20	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.

PMEG4020EPK

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40 V, 2 A low VF MEGA Schottky barrier rectifier

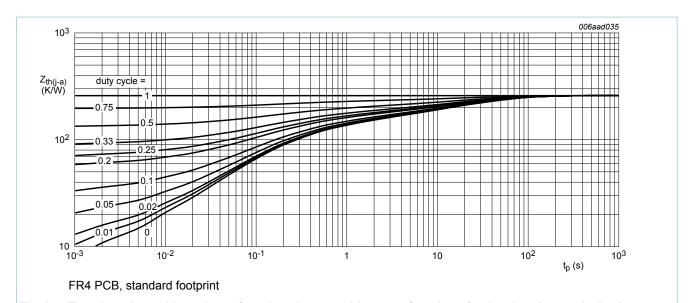


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

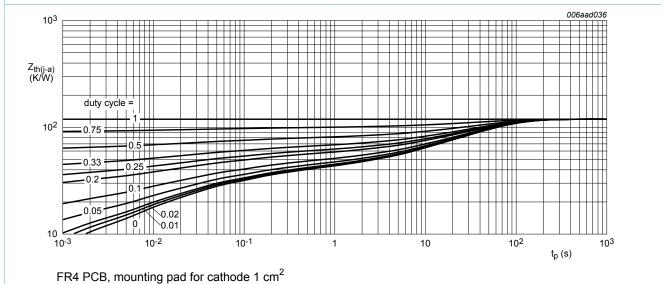
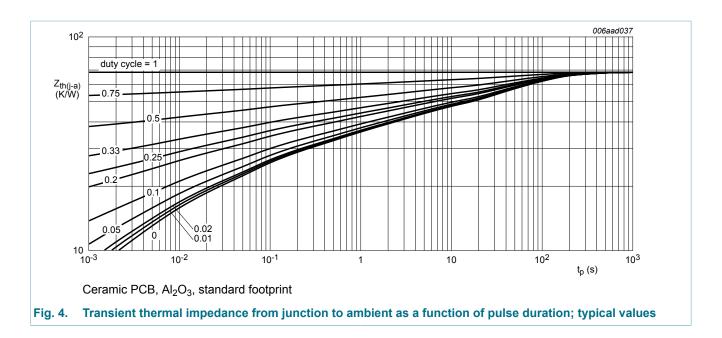


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

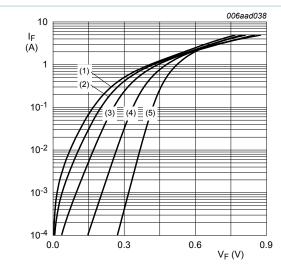
40 V, 2 A low VF MEGA Schottky barrier rectifier



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I_F = 100 mA; pulsed; $t_p \le$ 300 μs; $δ \le$ 0.02; T_j = 25 °C	-	330	380	mV
		I_F = 500 mA; pulsed; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	415	480	mV
		I_F = 1 A; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_j = 25 °C	-	490	550	mV
		I_F = 2 A; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_j = 25 °C	-	585	660	mV
I _R	reverse current	V _R = 10 V; T _j = 25 °C	-	1	5	μA
		V _R = 40 V; T _j = 25 °C	-	8	30	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	75	90	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	30	40	pF
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	4	-	ns
V_{FRM}	peak forward recovery voltage	$I_F = 0.5 \text{ A}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$	-	440	-	mV



(1)
$$T_i = 150 \, ^{\circ}C$$

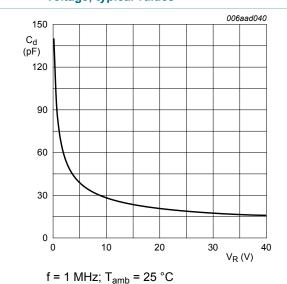
(2)
$$T_i = 125 \, ^{\circ}C$$

(3)
$$T_i = 85 \, ^{\circ}C$$

(4)
$$T_i = 25 \, ^{\circ}C$$

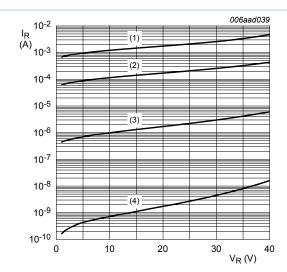
(5)
$$T_j = -40 \, ^{\circ}\text{C}$$

Fig. 5. Forward current as a function of forward voltage; typical values



r = r wir iz, r_{amb} = 25 C

Fig. 7. Diode capacitance as a function of reverse voltage; typical values



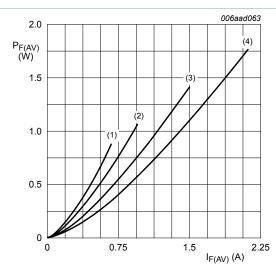
(1)
$$T_i = 125 \, ^{\circ}C$$

(2)
$$T_i = 85 \,^{\circ}C$$

(3)
$$T_j = 25 \, ^{\circ}C$$

(4)
$$T_i = -40 \, ^{\circ}C$$

Fig. 6. Reverse current as a function of reverse voltage; typical values



$$(1) \delta = 0.1$$

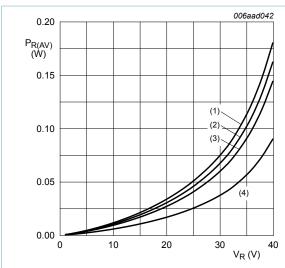
$$(2) \delta = 0.2$$

$$(3) \delta = 0.5$$

$$(4) \delta = 1$$

Fig. 8. Average forward power dissipation as a function of average forward current; typical values

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T_i = 125 °C

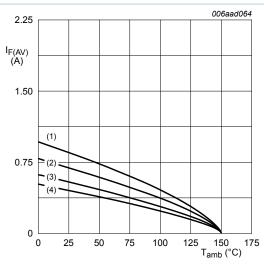
, (1) δ = 1

 $(2) \delta = 0.9$

 $(3) \delta = 0.8$

 $(4) \delta = 0.5$

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_i = 150 °C

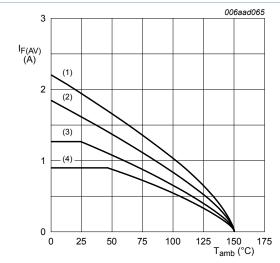
(1) δ = 1 (DC)

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

T_i = 150 °C

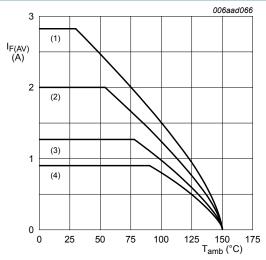
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

T_i = 150 °C

 $(1) \delta = 1 (DC)$

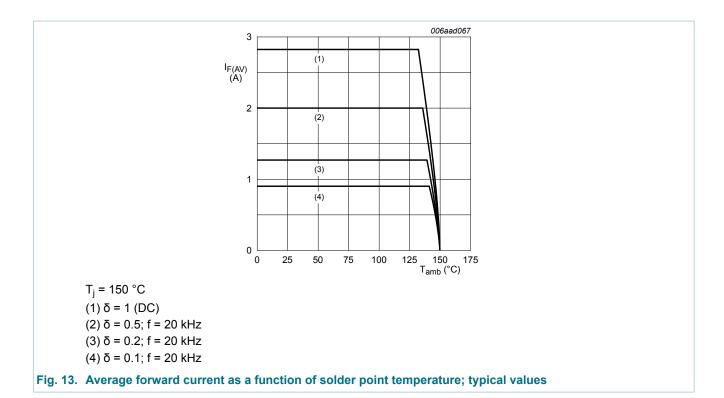
(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

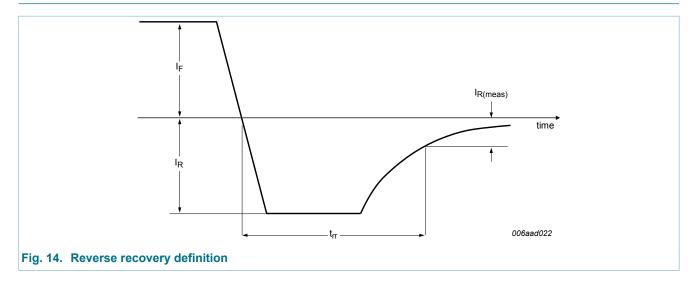
(4) $\delta = 0.1$; f = 20 kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values

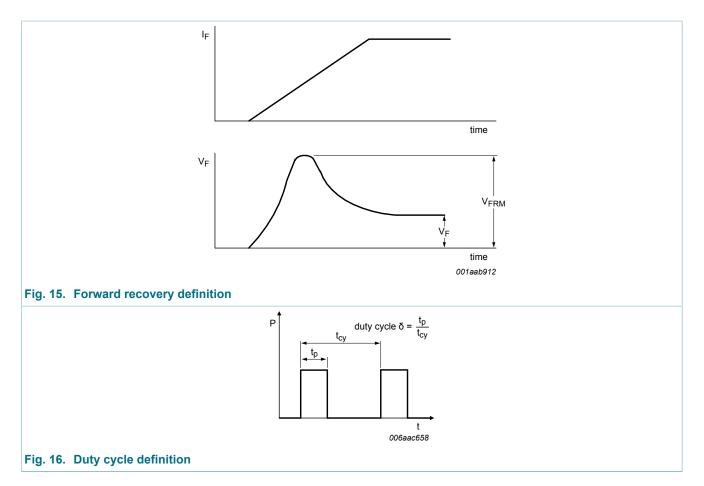
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11. Test information



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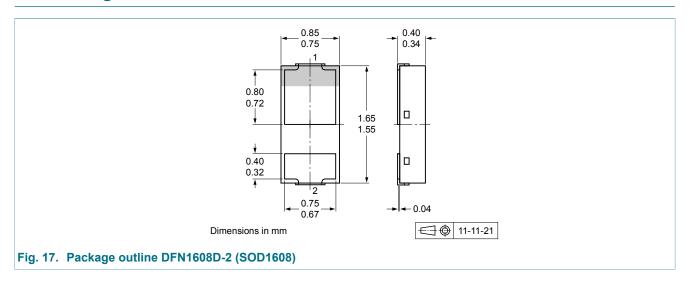
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

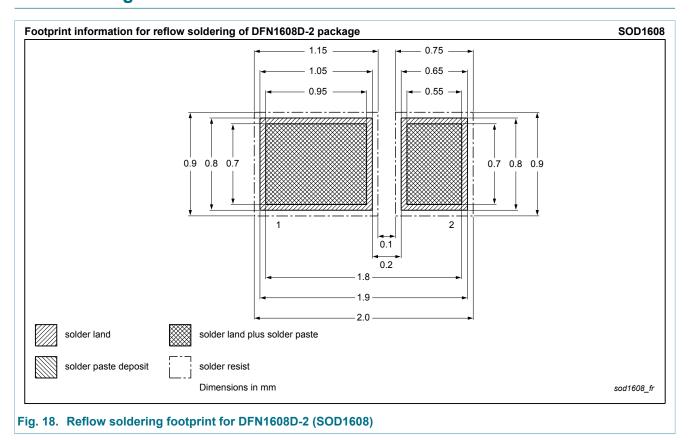
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMEG4020EPK v.2	20140211	Product data sheet	-	PMEG4020EPK v.1		
Modifications:	Marking code corrected					
PMEG4020EPK v.1	20120425	Product data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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